



BULK128D-B

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED

APPLICATIONS:

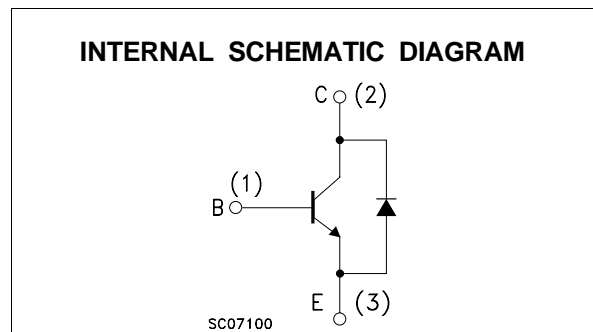
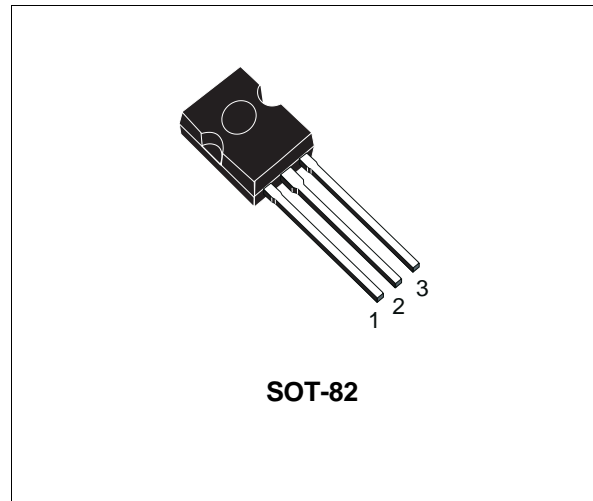
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS

DESCRIPTION

The device is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and medium voltage capability.

It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The device is designed for use in lighting applications and low cost switch-mode power supplies.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------|--|------------|------------|
| V_{CES} | Collector-Emitter Voltage ($V_{BE} = 0$) | 700 | V |
| V_{CEO} | Collector-Emitter Voltage ($I_B = 0$) | 400 | V |
| V_{EBO} | Emitter-Base Voltage ($I_C = 0$, $I_B = 2$ A, $t_p < 10\mu s$, $T_j < 150^\circ C$) | BV_{EBO} | V |
| I_C | Collector Current | 4 | A |
| I_{CM} | Collector Peak Current ($t_p < 5$ ms) | 8 | A |
| I_B | Base Current | 2 | A |
| I_{BM} | Base Peak Current ($t_p < 5$ ms) | 4 | A |
| P_{tot} | Total Dissipation at $T_c = 25^\circ C$ | 55 | W |
| T_{stg} | Storage Temperature | -65 to 150 | $^\circ C$ |
| T_j | Max. Operating Junction Temperature | 150 | $^\circ C$ |

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THERMAL DATA

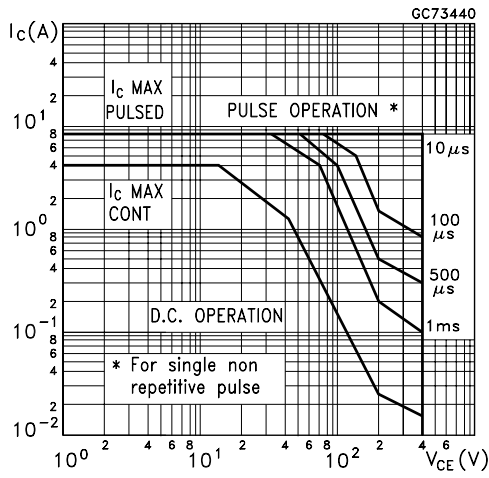
| | | | | |
|-----------------------|-------------------------------------|-----|------|------|
| R _{thj-case} | Thermal Resistance Junction-Case | Max | 2.27 | °C/W |
| R _{thj-amb} | Thermal Resistance Junction-Ambient | Max | 80 | °C/W |

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

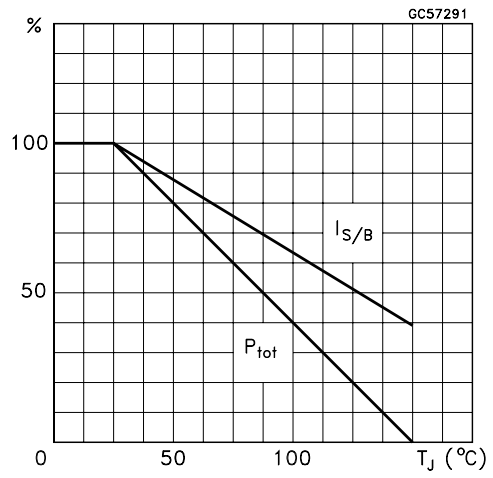
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------------------|---|---|---------|------------|-------------------|-------------|
| I _{CES} | Collector Cut-off Current (V _{BE} = -1.5 V) | V _{CE} = 700 V V _{CE} = 700 V T _C = 125 °C | | | 100 500 | μA μA |
| I _{CEO} | Collector-Emitter Leakage Current (I _B = 0) | V _{CE} = 400 V | | | 250 | μA |
| BV _{EBO} | Emitter-Base Breakdown Voltage (I _C = 0) | I _E = 10 mA | 9 | | 18 | V |
| V _{CEO(sus)} * | Collector-Emitter Sustaining Voltage (I _B = 0) | I _C = 100 mA L = 25 mH | 400 | | | V |
| V _{CE(sat)} * | Collector-Emitter Saturation Voltage | I _C = 0.5 A I _B = 0.1 A I _C = 1 A I _B = 0.2 A I _C = 2.5 A I _B = 0.5 A | | | 0.7 1 1.5 | V V V |
| V _{BE(sat)} * | Base-Emitter Saturation Voltage | I _C = 0.5 A I _B = 0.1 A I _C = 1 A I _B = 0.2 A I _C = 2.5 A I _B = 0.5 A | | | 1.1 1.2 1.3 | V V V |
| h _{FE} * | DC Current Gain | I _C = 10 mA V _{CE} = 5 V I _C = 2 A V _{CE} = 5 V | 10 8 | | 40 | |
| V _f | Forward Voltage Drop | I _f = 2 A | | | 2.5 | V |
| t _s t _f | RESISTIVE LOAD Storage Time Fall Time | V _{CC} = 250 V I _C = 2 A I _{B1} = 0.4 A I _{B2} = -0.4 A T _p = 30 μs (see fig. 2) | 2 | 0.2 | 2.9 | μs μs |
| t _s t _f | INDUCTIVE LOAD Storage Time Fall Time | V _{CC} = 200 V I _C = 2 A I _{B1} = 0.4 A V _{BE(off)} = -5 V R _{BB} = 0 Ω L = 200 μH (see fig. 1) | | 0.6 0.1 | | μs μs |

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

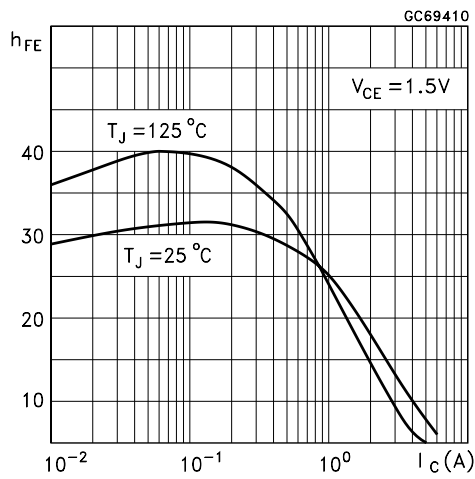
Safe Operating Areas



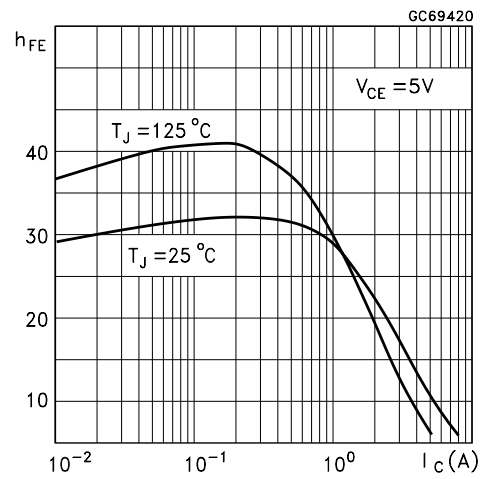
Derating Curve



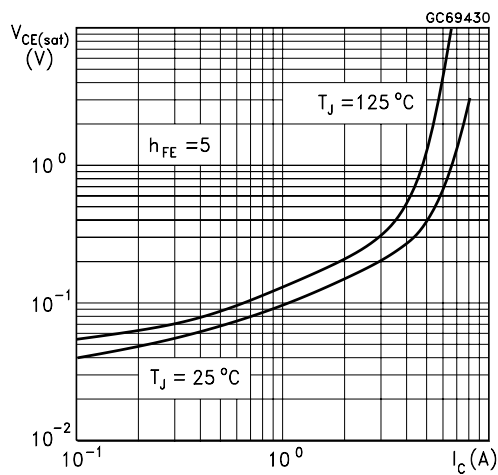
DC Current Gain



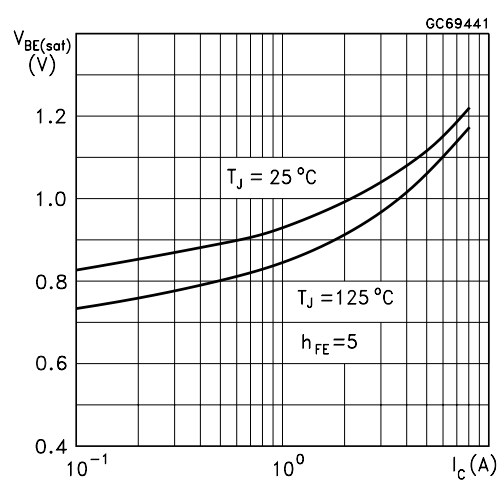
DC Current Gain



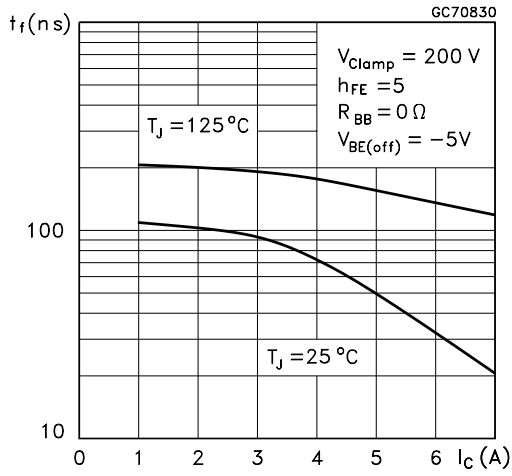
Collector Emitter Saturation Voltage



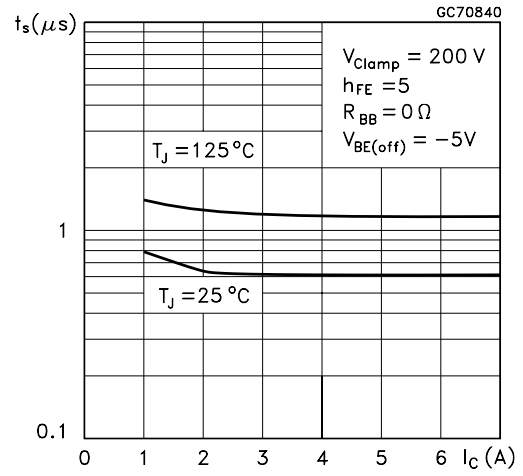
Base Emitter Saturation Voltage



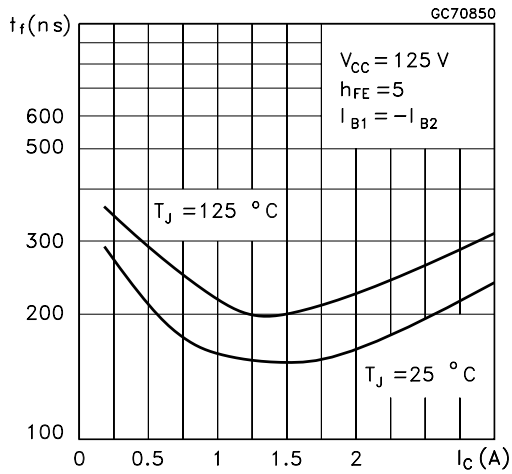
Inductive Fall Time



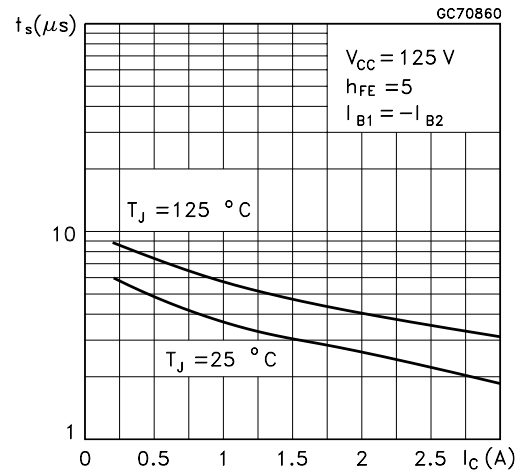
Inductive Storage Time



Resistive Load Fall Time



Resistive Load Storage Time



Reverse Biased SOA

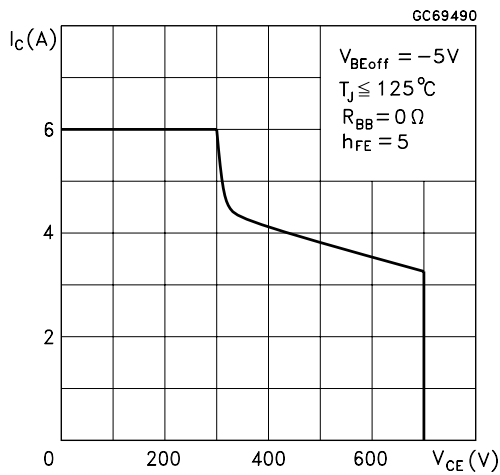


Figure 1: Inductive Load Switching Test Circuit.

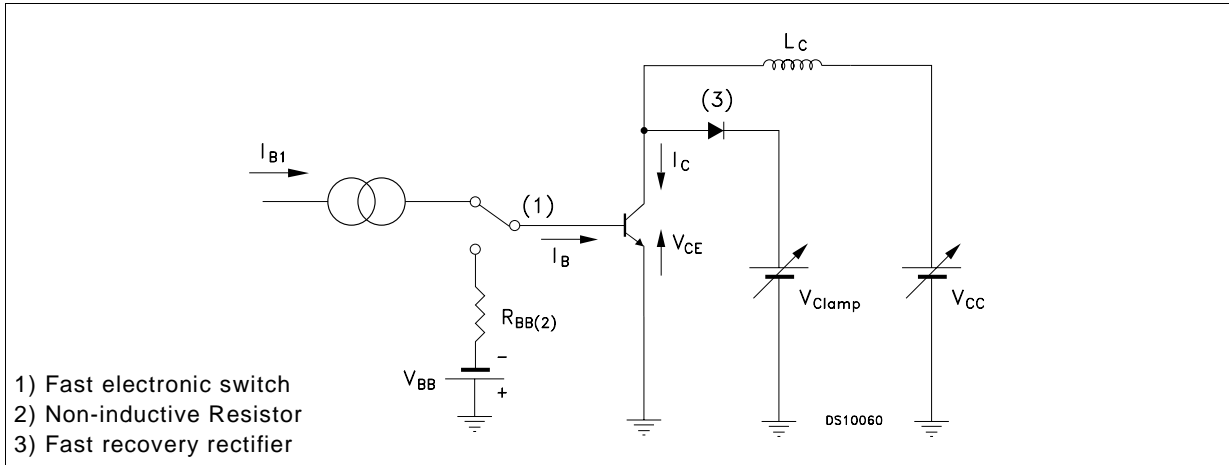
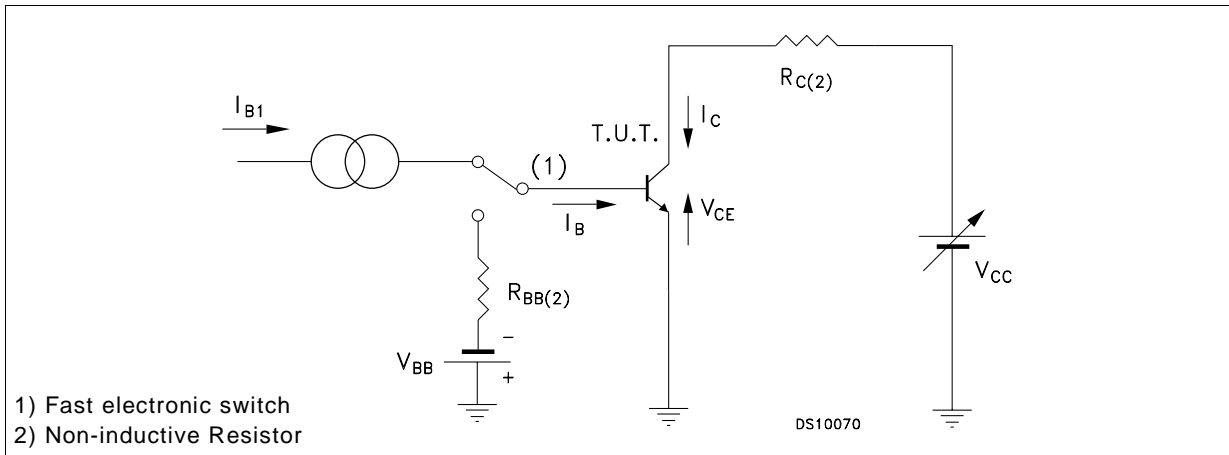
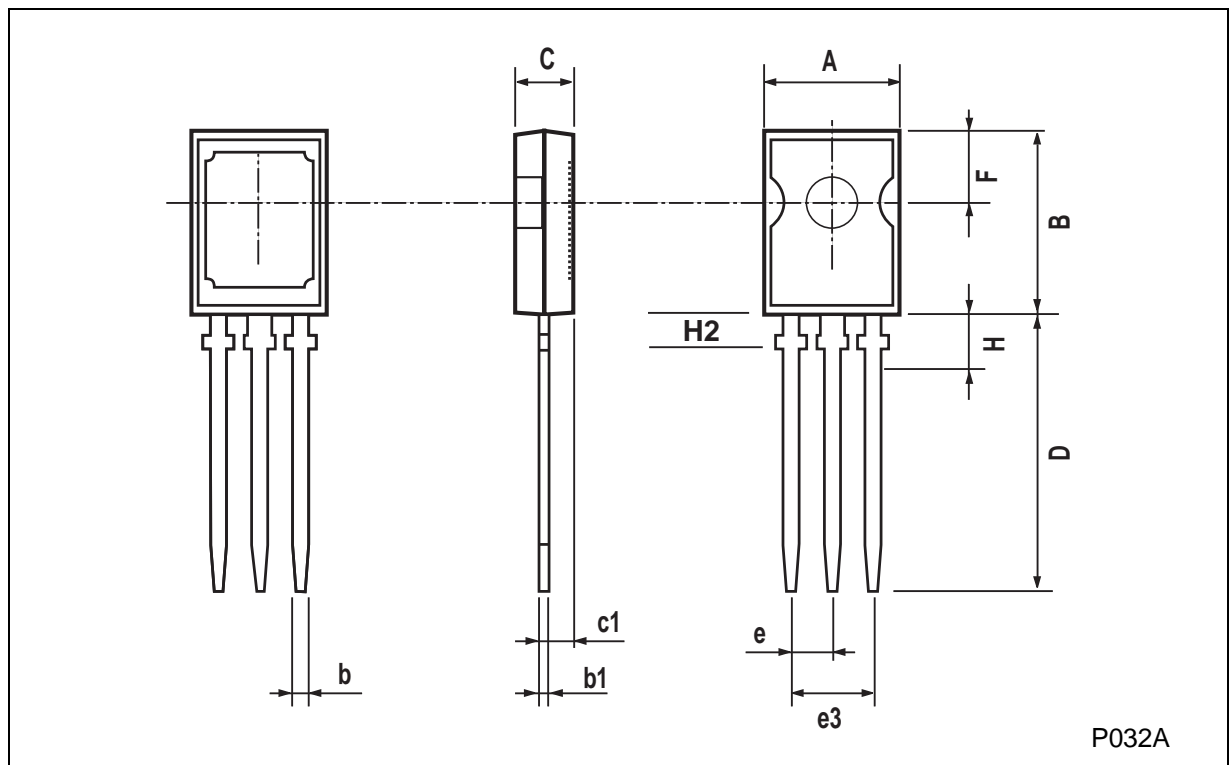


Figure 2: Resistive Load Switching Test Circuit.



SOT-82 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 7.4 | | 7.8 | 0.291 | | 0.307 |
| B | 10.5 | | 10.8 | 0.413 | | 0.444 |
| b | 0.7 | | 0.9 | 0.028 | | 0.035 |
| b1 | 0.49 | | 0.75 | 0.019 | | 0.030 |
| C | 2.4 | | 2.7 | 0.04 | | 0.106 |
| c1 | 1.0 | | 1.3 | 0.039 | | 0.05 |
| D | 15.4 | | 16 | 0.606 | | 0.629 |
| e | | 2.2 | | | 0.087 | |
| e3 | 4.15 | | 4.65 | 0.163 | | 0.183 |
| F | | 3.8 | | | 0.150 | |
| H | | | 2.54 | | 0.100 | |
| H2 | | 2.15 | | | 0.084 | |



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